

Jeffrey H Warner

List of Publications by Year in descending order

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260
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#	ARTICLE	IF	CITATIONS
1	Comparison of Single-Event Transients in SiGe HBTs on Bulk and Thick-Film SOI. IEEE Transactions on Nuclear Science, 2020, 67, 71-80.	2.0	7
2	New Approach for Pulsed-Laser Testing That Mimics Heavy-Ion Charge Deposition Profiles. IEEE Transactions on Nuclear Science, 2020, 67, 81-90.	2.0	16
3	Tradeoffs Between RF Performance and SET Robustness in Low-Noise Amplifiers in a Complementary SiGe BiCMOS Platform. IEEE Transactions on Nuclear Science, 2020, 67, 1521-1529.	2.0	3
4	Optimizing Optical Parameters to Facilitate Correlation of Laser- and Heavy-Ion-Induced Single-Event Transients in SiGe HBTs. IEEE Transactions on Nuclear Science, 2019, 66, 359-367.	2.0	15
5	A Low-Power, Real-Time Displacement Damage Dosimeter. IEEE Transactions on Nuclear Science, 2019, 66, 290-298.	2.0	3
6	The Effects of Temperature on the Single-Event Transient Response of a High-Voltage (>30 V) Complementary SiGe-on-SOI Technology. IEEE Transactions on Nuclear Science, 2019, 66, 389-396.	2.0	1
7	Best Practices for Using Electrostatic Discharge Protection Techniques for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2019, 66, 240-247.	2.0	3
8	Using Bessel beams and two-photon absorption to predict radiation effects in microelectronics. Optics Express, 2019, 27, 37652.	3.4	9
9	Utilizing SiGe HBT Power Detectors for Sensing Single-Event Transients in RF Circuits. IEEE Transactions on Nuclear Science, 2018, 65, 239-248.	2.0	8
10	Experimental Validation of an Equivalent LET Approach for Correlating Heavy-Ion and Laser-Induced Charge Deposition. IEEE Transactions on Nuclear Science, 2018, 65, 1724-1733.	2.0	25
11	SiGe HBT Profiles With Enhanced Inverse-Mode Operation and Their Impact on Single-Event Transients. IEEE Transactions on Nuclear Science, 2018, 65, 399-406.	2.0	9
12	A Simplified Approach for Predicting Pulsed-Laser-Induced Carrier Generation in Semiconductor. IEEE Transactions on Nuclear Science, 2017, 64, 1006-1013.	2.0	18
13	Strong Correlation Between Experiment and Simulation for Two-Photon Absorption Induced Carrier Generation. IEEE Transactions on Nuclear Science, 2017, 64, 1133-1136.	2.0	14
14	Single-Event Effects in High-Frequency Linear Amplifiers: Experiment and Analysis. IEEE Transactions on Nuclear Science, 2017, 64, 125-132.	2.0	5
15	The Impact of Technology Scaling on the Single-Event Transient Response of SiGe HBTs. IEEE Transactions on Nuclear Science, 2017, 64, 406-414.	2.0	22
16	Single-Event Measurement and Analysis of Antimony-Based p-Channel Quantum-Well MOSFETs With High- κ Dielectric. IEEE Transactions on Nuclear Science, 2017, 64, 434-440.	2.0	1
17	Using TCAD Modeling to Compare Heavy-Ion and Laser-Induced Single Event Transients in SiGe HBTs. IEEE Transactions on Nuclear Science, 2017, 64, 398-405.	2.0	24
18	Single-Event Effects in a Millimeter-Wave Receiver Front-End Implemented in 90 nm, 300 GHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2017, 64, 536-543.	2.0	5

#	ARTICLE	IF	CITATIONS
19	Single-Event Transient Response of Comparator Pre-Amplifiers in a Complementary SiGe Technology. IEEE Transactions on Nuclear Science, 2017, 64, 89-96.	2.0	8
20	An Investigation of Single-Event Effect Modeling Techniques for a SiGe RF Low-Noise Amplifier. IEEE Transactions on Nuclear Science, 2016, 63, 273-280.	2.0	16
21	Single Event Measurement and Analysis of Antimony Based n-Channel Quantum-Well MOSFET With High- κ Dielectric. IEEE Transactions on Nuclear Science, 2015, 62, 2807-2814.	2.0	3
22	Single-Event Effects in a W-Band (75-110GHz) Radar Down-Conversion Mixer Implemented in 90nm, 300GHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2015, 62, 2657-2665.	2.0	12
23	The Role of Negative Feedback Effects on Single-Event Transients in SiGe HBT Analog Circuits. IEEE Transactions on Nuclear Science, 2015, 62, 2599-2605.	2.0	4
24	Two-Photon Absorption Induced Single-Event Effects: Correlation Between Experiment and Simulation. IEEE Transactions on Nuclear Science, 2015, 62, 2867-2873.	2.0	18
25	Simulation of Laser-Based Two-Photon Absorption Induced Charge Carrier Generation in Silicon. IEEE Transactions on Nuclear Science, 2015, 62, 1550-1557.	2.0	18
26	A Dosimetry Methodology for Two-Photon Absorption Induced Single-Event Effects Measurements. IEEE Transactions on Nuclear Science, 2014, 61, 3416-3423.	2.0	30
27	Simulation of Light-Matter Interaction and Two-Photon Absorption Induced Charge Deposition by Ultrashort Optical Pulses in Silicon. IEEE Transactions on Nuclear Science, 2014, 61, 3504-3511.	2.0	15
28	On the Transient Response of a Complementary (nnp) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 Transactions on Nuclear Science, 2014, 61, 3146-3153.	2.0	15
29	Design of Radiation-Hardened RF Low-Noise Amplifiers Using Inverse-Mode SiGe HBTs. IEEE Transactions on Nuclear Science, 2014, 61, 3218-3225.	2.0	34
30	Evaluating the Effects of Single Event Transients in FET-Based Single-Pole Double-Throw RF Switches. IEEE Transactions on Nuclear Science, 2014, 61, 756-765.	2.0	12
31	RHBD Technique for Single-Event Charge Cancellation in Folded-Cascode Amplifiers. IEEE Transactions on Nuclear Science, 2013, 60, 2756-2761.	2.0	12
32	Single-Event Upsets in Substrate-Etched CMOS SOI SRAMs Using Ultraviolet Optical Pulses With Sub-Micrometer Spot Size. IEEE Transactions on Nuclear Science, 2013, 60, 4184-4191.	2.0	13
33	An Investigation of Single-Event Effects and Potential SEU Mitigation Strategies in Fourth-Generation, 90nm SiGe BiCMOS. IEEE Transactions on Nuclear Science, 2013, 60, 4175-4183.	2.0	20
34	Correlation of Telemetered Solar Array Data With Particle Detector Data On GPS Spacecraft. IEEE Transactions on Nuclear Science, 2011, 58, 3118-3125.	2.0	27
35	Comparison of Single and Two-Photon Absorption for Laser Characterization of Single-Event Upsets in SOI SRAMs. IEEE Transactions on Nuclear Science, 2011, 58, 2968-2975.	2.0	10
36	Evaluating the Influence of Various Body-Contacting Schemes on Single Event Transients in 45-nm SOI CMOS. IEEE Transactions on Nuclear Science, 2010, , .	2.0	10